

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

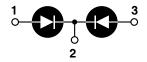
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

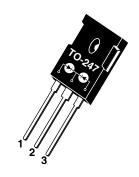








- 1 Anode 1
- 2 Common Cathode Back of Case - Cathode
- 3-Anode 2





Fully compliant with RoHS 2002/95 Directive.

HIGH VOLTAGE SCHOTTKY DIODE

PRODUCT APPLICATIONS	PRODUCT FEATURES	PRODUCT BENEFITS
Parallel Diode	• Ultrafast Recovery Times	• Low Losses
-Switchmode Power Supply -Inverters	Soft Recovery Characteristics	• Low Noise Switching
Free Wheeling Diode -Motor Controllers	Popular TO-247 Package	Cooler Operation
-Converters • Snubber Diode	• Low Forward Voltage	Higher Reliability Systems
Uninterruptible Power Supply (UPS)48 Volt Output Rectifiers	High Blocking Voltage	Increased System Power Density
High Speed Rectifiers	Low Leakage Current	Density

MAXIMUM RATINGS All Ratings Are Per Leg: $T_C = 25^{\circ}C$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT30S20BCTG	UNIT	
V _R	Maximum D.C. Reverse Voltage			
V _{RRM}	Maximum Peak Repetitive Reverse Voltage	200	Volts	
V _{RWM}	Maximum Working Peak Reverse Voltage			
I _F (AV)	Maximum Average Forward Current (T _C = 125°C, Duty Cycle = 0.5)	45		
I _F (RMS)	RMS Forward Current (Square wave, 50% duty)	121	Amps	
I _{FSM}	Non-Repetitive Forward Surge Current (T _J = 45°C, 8.3ms)	320		
T _J ,T _{STG}	Operating and StorageTemperature Range	-55 to 150	°C	
T _L	Lead Temperature Case for 10 Sec.	300		
E _{VAL}	Avalanche Energy (2A, 15mH)	30	mJ	

STATIC FLECTRICAL CHARACTERISTICS

STATIC ELECTRICAL CHARACTERISTICS						
Symbol			MIN	TYP	MAX	UNIT
V _F		I _F = 30A		.80	.85	Volts
		I _F = 60A		.91		
		I _F = 30A, T _J = 125°C		.67		
I _{RM}	Maximum Reverse Leakage Current	V _R = V _R Rated			0.5	mA
		$V_R = V_R$ Rated, $T_J = 125$ °C			15	
C _T	Junction Capacitance, V _R = 200V			150		pF



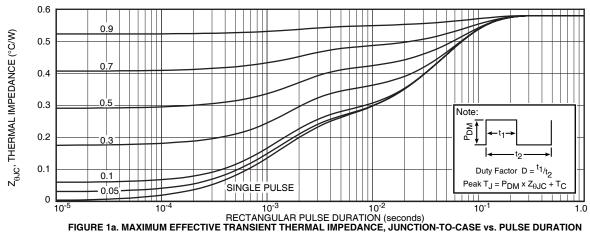
Pb) Fully complient with RoHS 2002/95 Directive.

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t _{rr}	Reverse Recovery Time	1 20 A di /dt 200 A ///2	-	55		ns
Q _{rr}	Reverse Recovery Charge	$I_F = 30A$, $di_F/dt = -200A/\mu s$ $V_R = 133V$, $T_C = 25^{\circ}C$	-	190		nC
I _{RRM}	Maximum Reverse Recovery Current		-	6	-	Amps
t _{rr}	Reverse Recovery Time	I _F = 30A, di _F /dt = -200A/μs V _R = 133V, T _C = 125°C	-	100		ns
Q _{rr}	Reverse Recovery Charge		-	450		nC
I _{RRM}	Maximum Reverse Recovery Current		•	9	-	Amps
t _{rr}	Reverse Recovery Time	$I_F = 30A$, $di_F/dt = -700A/\mu s$ $V_R = 133V$, $T_C = 125^{\circ}C$	1	70		ns
Q _{rr}	Reverse Recovery Charge		-	960		nC
I _{RRM}	Maximum Reverse Recovery Current		-	24		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{ hetaJC}$	Junction-to-Case Thermal Resistance			.58	°C/W
R_{\thetaJA}	Junction-to-Ambient Thermal Resistance			40	
W _T	Package Weight		0.22		oz
			5.9		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

APT Reserves the right to change, without notice, the specifications and information contained herein.



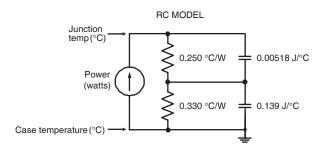
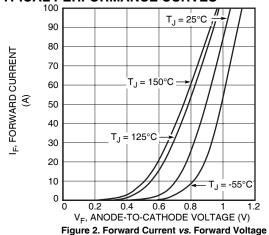


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

TYPICAL PERFORMANCE CURVES



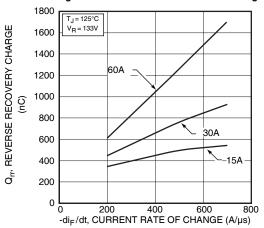


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

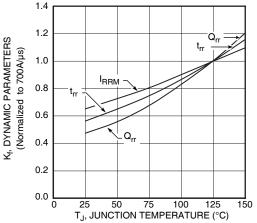


Figure 6. Dynamic Parameters vs. Junction Temperature

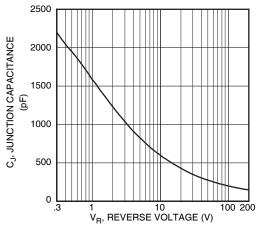


Figure 8. Junction Capacitance vs. Reverse Voltage

APT30S20BCTG

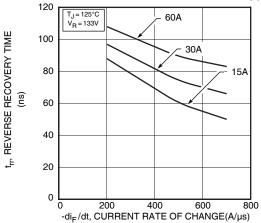


Figure 3. Reverse Recovery Time vs. Current Rate of Change

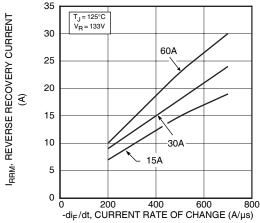


Figure 5. Reverse Recovery Current vs. Current Rate of Change

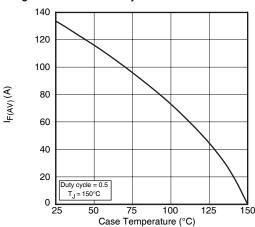


Figure 7. Maximum Average Forward Current vs. CaseTemperature

0.25 I_{RRM}

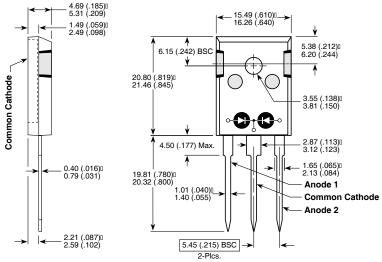
6

Figure 9. Diode Test Circuit

- 1 I_F Forward Conduction Current
- 2 di_E/dt Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} Maximum Reverse Recovery Current.
- 4 t_{rr} Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and 0.25•I_{RRM} passes through zero.
- 5 Q_{rr} Area Under the Curve Defined by I_{RRM} and t_{rr}.

Figure 10, Diode Reverse Recovery Waveform and Definitions

TO-247 Package Outline



Dimensions in Millimeters and (Inches)